



Features

- Solid State
- Small Size
- 5 Watts Output
- Internal Regulator/Active Bias

Options

- Other Frequencies
- Other Bandwidths
- Coupled Output Port

High Power Amplifiers

XS1287



Description

Designed as driver amplifiers in Radar systems, and power amplifiers in test systems, these amplifiers utilize GaAs FET devices to achieve excellent power output.



Model	XS1287	Units
Frequency	9.75-10.25	GHz
Gain	25 +/- 1.0	dB
Power Sat	5	watt
P1dB GCP	4	watt
VSWR in (max)	2.0:1	
VSWR out (max)	1.5:1	
Voltage	+12	VDC
Current	2700	mA
Voltage	-5	VDC
Current	50	mA

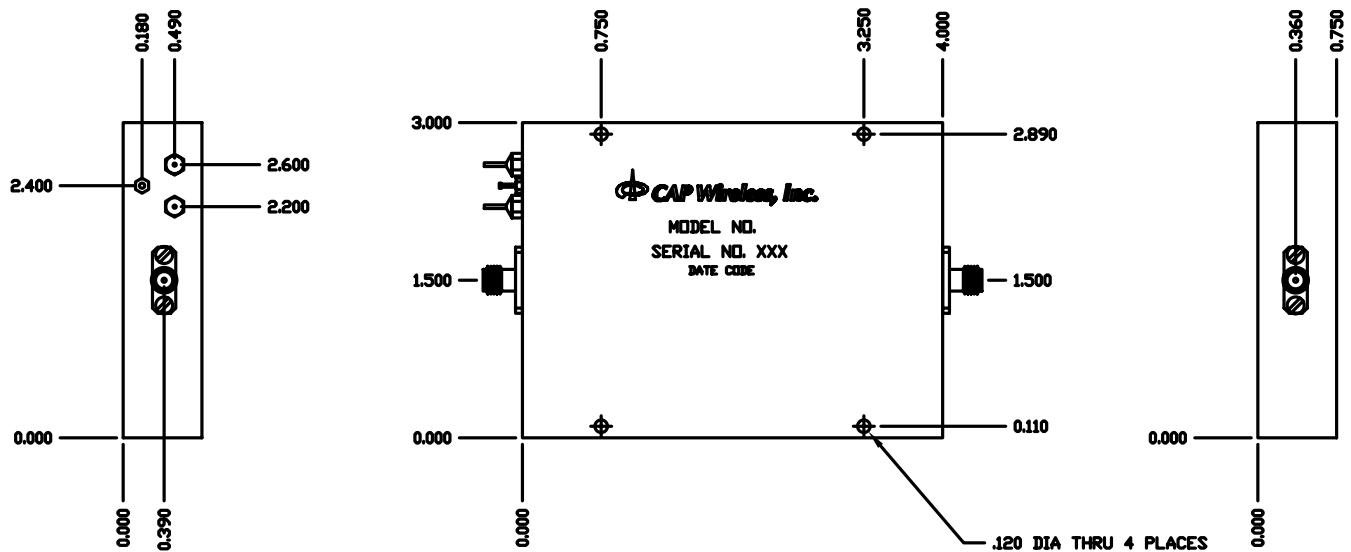
Operating temperature: +10 to +50°C.
 Storage temperature: -50 to +85°C
 Input/Output Connectors: -SMA "F"



High Power Amplifiers

XS1287

Outline Drawing



Company Design Philosophy

Essential to the company's strategy is the use of the latest and most sophisticated design software available. These design tools include complete suites of HP-EEsof, and AWR- Microwave Office, circuit and system high frequency EDA tools. The company consistently achieves its goal of accurately creating "prototypes" in software, as evidenced by its ability to go directly from a simulated design to deliverable prototypes and rapidly ramp to fulfill volume requirements. A crucial element of the company's development philosophy is to "design for production" to drastically improve manufacturability by virtually eliminating tuning and adjustments as part of the manufacturing process. The result is lower cost, higher reliability products with predictable delivery times.

The products shown on these data sheets are merely a representation of the company's capabilities, where a library of designs is available to draw upon to meet specific customer performance requirements. If you have a unique requirement, contact the factory to explore the latest in technology.